

isc N-Channel MOSFET Transistor

IPD65R1K4CFD, IIPD65R1K4CFD

• FEATURES

- Static drain-source on-resistance:
 $R_{ds(on)} \leq 1.4\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

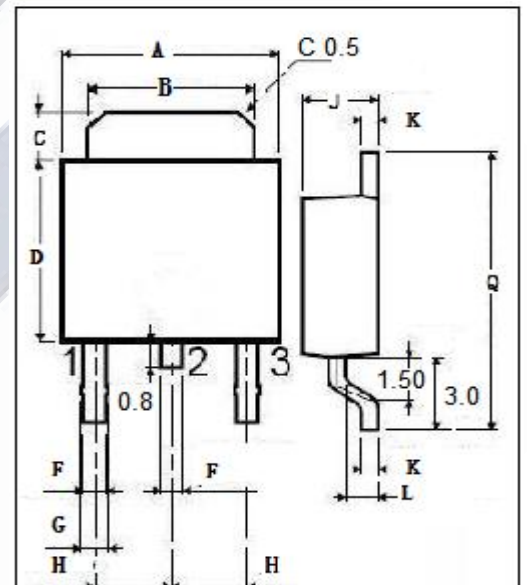
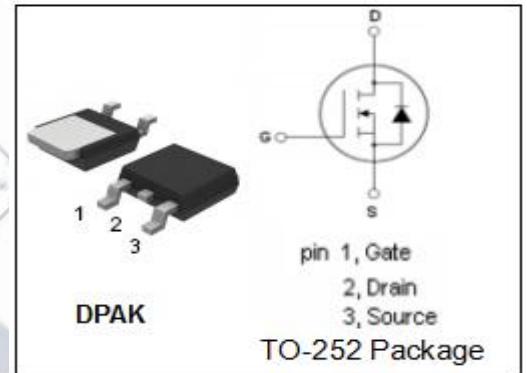
- Fast switching
- Very high commutation ruggedness

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	2.8	A
I_{DM}	Drain Current-Single Pulsed	8.2	A
P_D	Total Dissipation @ $T_c=25^\circ\text{C}$	28.4	W
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Channel-to-case thermal resistance	4.4	$^\circ\text{C/W}$
$R_{th(j-a)}$	Channel-to-ambient thermal resistance	62	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

isc N-Channel MOSFET Transistor
IPD65R1K4CFD, IIPD65R1K4CFD
ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	650			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =0.1mA	3.5		4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =1A			1.4	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =650V; V _{GS} =0V			1	μA
V _{SD}	Diode forward voltage	I _F =1.5A, V _{GS} =0V		0.9		V